

. reescale Semiconductor Technical Data

Gallium Arsenide CATV Amplifier Module

Features

- Specified for 79-, 112- and 132-Channel Loading
- **Excellent Distortion Performance**
- Built-in Input Diode Protection
- GaAs FET Transistor Technology
- Unconditionally Stable Under All Load Conditions
- Improved Ruggedness

Applications

- CATV Systems Operating in the 40 to 870 MHz Frequency Range
- Input Stage Amplifier in Optical Nodes, Line Extenders and Trunk Distribution Amplifiers for CATV Systems
- Output Stage Amplifier on Applications Requiring Low Power Dissipation and High Output Performance
- Driver Amplifier in Linear General Purpose Applications

Description

- 24 Vdc Supply, 40 to 870 MHz, CATV GaAs Forward Amplifier Module
- Replaced MHW9186A. There are no form, fit or function changes with this part replacement.
- **RoHS Compliant**

Document Number: MHW9186AN Rev. 3, 5/2006

MHW9186AN

870 MHz **18.5 dB GAIN** 132-CHANNEL **GaAs CATV AMPLIFIER MODULE**



CASE 1302-01, STYLE 1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
RF Voltage Input (Single Tone)	V _{in}	+65	dBmV
DC Supply Voltage	V _{CC}	+26	Vdc
Operating Case Temperature Range	T _C	-20 to +100	°C
Storage Temperature Range	T _{stg}	-40 to +100	°C

Table 2. ESD Maximum Ratings

Rating	Input Value	Output Value	Unit
Surge Voltage per IEC 1000-4-5	300	300	V
Human Body Model per Mil. Std. 1686	2	2	kV

Table 3. Electrical Characteristics (V_{CC} = 24 Vdc, T_{C} = +30°C, 75 Ω system unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Frequency Range		BW	40	_	870	MHz
Power Gain	870 MHz	G _p	18	18.5	19.5	dB
Slope	40-870 MHz	S	0.1	0.6	1.2	dB
Gain Flatness (40-870 MHz, Peak-to-Valley)		G _F	_	0.3	0.8	dB
Return Loss — Input		IRL				dB
(Z _o = 75 Ohms)	40-200 MHz		20		_	
	200-600 MHz		19	_	_	
	600-870 MHz		18	_	_	
Return Loss — Output		ORL				dB
(Z _o = 75 Ohms)	40-200 MHz		20		_	
	200-600 MHz		19	_	_	
	600-870 MHz		18	_	_	



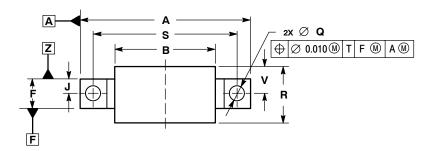
Table 3. Electrical Characteristics (V_{CC} = 24 Vdc, T_{C} = +30°C, 75 Ω system unless otherwise noted) (continued)

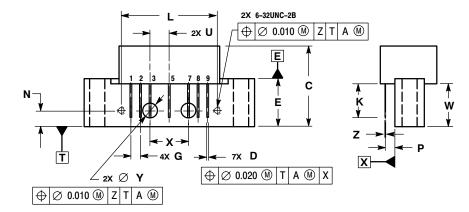
Characteristic			Min	Тур	Max	Unit
Composite Second Order						dBc
(V _{out} = +44 dBmV/ch., Worst Case)	132-Channel FLAT	CSO ₁₃₂	_	-67	-60	
(V _{out} = +46 dBmV/ch., Worst Case)	112-Channel FLAT	CSO ₁₁₂		-65	-61	
(V _{out} = +48 dBmV/ch., Worst Case)	79-Channel FLAT	CSO ₇₉	_	-72	-64	
Cross Modulation Distortion @ Ch 2						dBc
$(V_{out} = +44 \text{ dBmV/ch.}, FM = 55 \text{ MHz})$	132-Channel FLAT	XMD ₁₃₂		-58	-52	
$(V_{out} = +46 \text{ dBmV/ch.}, FM = 55 \text{ MHz})$	112-Channel FLAT	XMD ₁₁₂		-58	-52	
$(V_{out} = +48 \text{ dBmV/ch.}, FM = 55 \text{ MHz})$	79-Channel FLAT	XMD ₇₉	_	-58	-52	
Composite Triple Beat						dBc
(V _{out} = +44 dBmV/ch., Worst Case)	132-Channel FLAT	CTB ₁₃₂		-62	-58	
(V _{out} = +46 dBmV/ch., Worst Case)	112-Channel FLAT	CTB ₁₁₂	_	-61	-58	
(V _{out} = +48 dBmV/ch., Worst Case)	79-Channel FLAT	CTB ₇₉	_	-64	-60	
Noise Figure	50 MHz	NF	_	4.6	6.0	dB
	870 MHz		_	3.7	6.0	
DC Current (V_{DC} = 24 V, T_{C} = -20° to +100°	C)	I _{DC}	230	250	265	mA



ARCHIVE INFORMATION

PACKAGE DIMENSIONS





- NOTES:
 1. DIMENSIONS ARE IN INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α		1.775		45.085	
В		1.085		27.559	
С		0.840		21.336	
D	0.015	0.021	0.381	0.533	
E	0.465	0.510	11.811	12.954	
F	0.300	0.325	7.62	8.255	
G	0.100 BSC		2.540 BSC		
J	0.156	BSC	3.962 BSC		
K	0.315	0.355	8.001	9.017	
L	1.000 BSC		25.400 BSC		
N	0.165 BSC		4.191 BSC		
P	0.100 BSC		2.540 BSC		
Q	0.148	0.168	3.759	4.267	
R		0.600		15.24	
S	1.500 BSC		38.100 BSC		
U	0.200 BSC		5.080 BSC		
V		0.250		6.350	
W	0.435		11.049		
X	0.400 BSC		10.160 BSC		
Y	0.152	0.163	3.861	4.140	
Z	0.009	0.011	0.229	0.279	

- STYLE 1:
 PIN 1. RF INPUT
 2. GROUND
 3. GROUND
 4. DELETED
 5. VDC
 6. DELETED
 7. GROUND
 8. GROUND
 9. RF OUTPUT

CASE 1302-01 ISSUE E



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